

LISTING OF THE CLAIMS

The following Listing of the Claims replaces all prior Listings of the Claims within this application.

1. (Original) A method of fabricating a silicon-on-insulator (SOI) substrate comprising:

providing a structure comprising at least a Si-containing substrate that has a region of vacancies or voids located therein;

implanting oxygen ions into said structure using an oxygen dose of about $1\text{E}17$ atoms/cm² or less; and

annealing the structure containing implanted oxygen ions and vacancies or voids to form a silicon-on-insulator that includes a Si-containing over-layer and a buried oxide, said buried oxide having a thickness of about 100 nm or less.

2. (Original) The method of Claim 1 wherein said Si-containing substrate is a doped substrate containing n- or p-type dopants.

3. (Original) The method of Claim 2 wherein said Si-containing substrate is a p-type substrate.

4. (Currently Amended) The method of Claim 1 wherein said providing ~~step comprises the~~ structure comprises using an electrolytic anodization process for forming the region of voids or vacancies within the Si-containing substrate.

5. (Original) The method of Claim 4 wherein said electrolytic anodization process is performed in the presence of a HF-containing solution.

6. (Currently Amended) The method of Claim 4 wherein the electrolytic anodization process is

performed using a constant current source operating at a current density of from about 0.05 to about 50 milliAmps/cm².

7. (Original) The method of Claim 1 wherein said region of vacancies or voids is a porous Si-containing region that has a porosity of about 0.01% or greater.

8. (Currently Amended) The method of Claim 1 further comprising forming a ~~single-crystal~~ Si-containing layer upon the Si-containing substrate between said providing the structure and said implanting oxygen steps.

9. (Currently Amended) The method of Claim 8 wherein said ~~single-crystal~~ Si-containing layer comprises epitaxial Si, amorphous Si, SiGe, single or polycrystalline Si or any combinations thereof.

10. (Currently Amended) The method of Claim 1 further comprising ~~a bake-step~~ baking the structure between said providing and said implanting steps, with or without subsequent Si-containing layer growth.

11. (Currently Amended) The method of Claim 10 wherein said ~~bake-step~~ baking the structure is performed in a hydrogen-containing ambient at a temperature from about 800° to about 1200°C.

12. (Currently Amended) The method of Claim 1 wherein said implanting step is performed at an oxygen dose from about 1E16 to about 1E17 atoms/cm².

13. (Original) The method of Claim 1 wherein said implanting step is performed using a beam current density from about 0.05 to about 500 milliAmps/cm², an energy from about 40 to about 1000 keV, and a temperature from about 200° to about 600° C.

14. (Original) The method of Claim 1 wherein said implanting step is a blanket implant process.

15. (Original) The method of Claim 1 wherein said implanting step is a patterned implant process.

16. (Original) The method of Claim 1 wherein said implanting step further comprises a second oxygen implant step.

17. (Original) The method of Claim 16 wherein said second implant step is performed at an oxygen dose from about 1×10^{14} to about 1×10^{16} atoms/cm² using a beam current density from about 0.05 to about 5 milliAmps/cm², an energy from about 40 to about 1000 keV, and a temperature from about 4K to about 200° C.

18. (Original) The method of Claim 1 wherein the annealing is performed in an oxygen-containing ambient.

19. (Original) The method of Claim 18 wherein the oxygen-containing ambient further comprises an inert gas.

20. (Original) The method of Claim 19 wherein the oxygen-containing ambient is selected from the group consisting of O₂, NO, N₂O, ozone, and air.

21. (Original) The method of Claim 1 wherein the annealing is performed at a temperature of from about 650°C to about 1350°C.

22. (Original) The method of Claim 1 wherein the annealing forms a surface oxide atop the Si-containing over-layer.

23. (Currently Amended) A method of fabricating a silicon-on-insulator (SOI) substrate comprising:

providing a structure comprising at least a Si-containing substrate that has a region of vacancies

or voids located therein;

forming a ~~single-crystal~~ Si-containing layer atop said structure;

implanting oxygen ions into said structure using an oxygen dose of about $1\text{E}17$ atoms/cm² or less; and

annealing the structure containing implanted oxygen ions and vacancies or voids to form a silicon-on-insulator that includes a Si-containing over-layer and a buried oxide, said buried oxide having a thickness of about 100 nm or less.

24. (Original) A method of fabricating a silicon-on-insulator (SOI) substrate comprising:

providing a structure comprising at least a Si-containing substrate that has a region of vacancies or voids located therein;

subjecting said structure to a bake step, said bake step is performed in a hydrogen-containing ambient;

implanting oxygen ions into said structure using an oxygen dose of about $1\text{E}17$ atoms/cm² or less; and

annealing the structure containing implanted oxygen ions and vacancies or voids to form a silicon-on-insulator that includes a Si-containing over-layer and a buried oxide, said buried oxide having a thickness of about 100 nm or less.

25. (Currently Amended) The method of Claim 24 further comprising forming a ~~single-crystal~~ Si-containing layer atop said structure, said forming said Si-containing layer occurs between said subjecting and said implanting steps.